

YJ Planar Schottky Barrier Diode Die Specification

200V 200A, 250mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB275H200AS-290A

Main Products Characterstics

- Average forward current: $I_F(AV) = 200\text{ A}$
- Maximum operating junction temperature: $T_j = 175\text{ }^{\circ}\text{C}$
- ESD rating: >8KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: AL

Maximum Ratings

Static Electrical Characteristics (Ta = 25°C)

$I_F = 200\text{ A}$
Pulse Test: $t_p = 300\text{ }\mu\text{s}$, $\delta \leq 2\%$

Device Schematics and Outline Drawing

Die Thickness *